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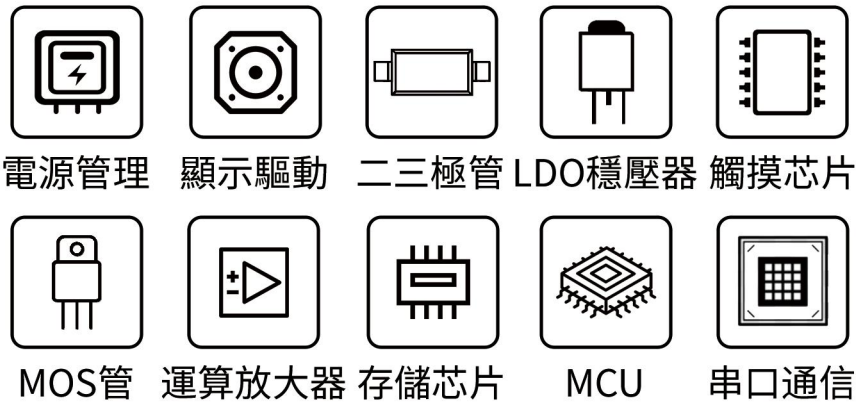
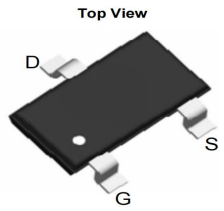


3401AJ-TD

產品規格說明書

General Description

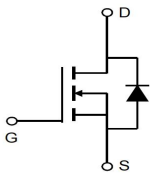
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge



SOT23

Features

- 30V, 4A
  $R_{DS(ON)}$ < 47mΩ @ V_{GS} = 10V
  $R_{DS(ON)}$ < 52mΩ @ V_{GS} = 4.5V
  $R_{DS(ON)}$ < 62mΩ @ V_{GS} = 2.5V



Applications

- Load Switch
- PWM Application
- Power Management

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		30	V
V_{GS}	Gate-to-Source Voltage		±12	V
I_D	Continuous Drain Current	T_A = 25°C	4	A
		T_A = 100°C	3	
I_{DM}	Pulsed Drain Current [1]		16	A
P_D	Power Dissipation	T_A = 25°C	1.2	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient[2]		103	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 30V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.5	1.0	1.4	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 4A	-	45	47	mΩ
		V_{GS} = 4.5V, I_D = 3A	-	48	52	mΩ
		V_{GS} = 2.5V, I_D = 2A	-	58	62	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	-	414	-	pF
C_{oss}	Output Capacitance		-	36	-	pF
C_{rss}	Reverse Transfer Capacitance		-	29	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 4.5V V_{DS} = 15V, I_D = 2A	-	4.5	-	nC
Q_{gs}	Gate Source Charge		-	1	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 4.5V, V_{DD} = 15V I_D= 2A, R_{GEN} = 3Ω	-	4	-	ns
t_r	Turn-On Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	41	-	ns
t_f	Turn-Off Fall Time		-	17	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 4A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 2A, di/dt = 100A/us	-	6	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	1	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

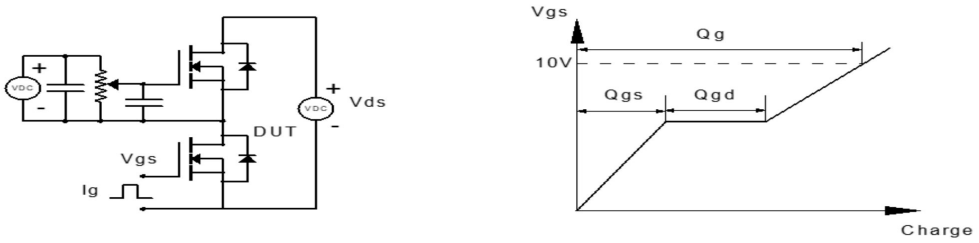


Figure 1: Gate Charge Test Circuit & Waveform

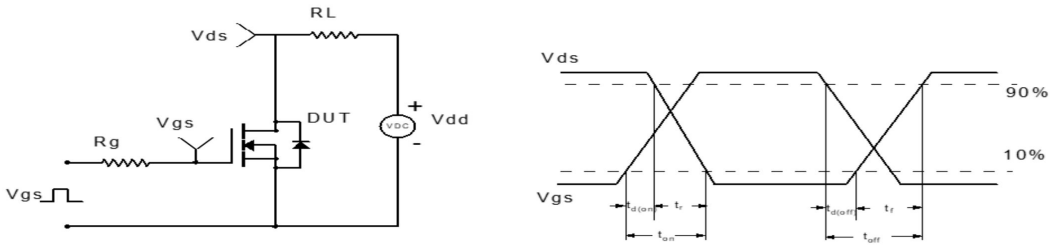


Figure 2: Resistive Switching Test Circuit & Waveform

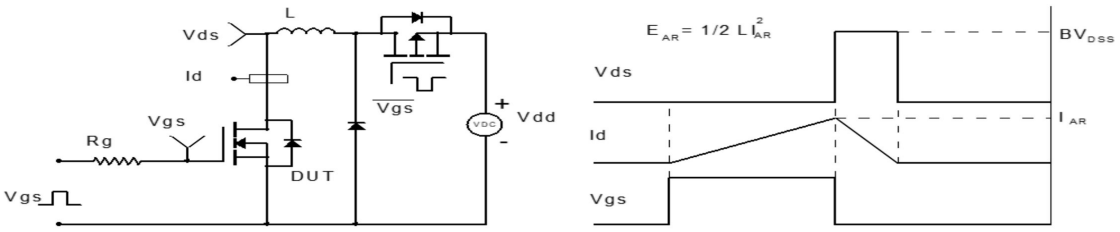


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

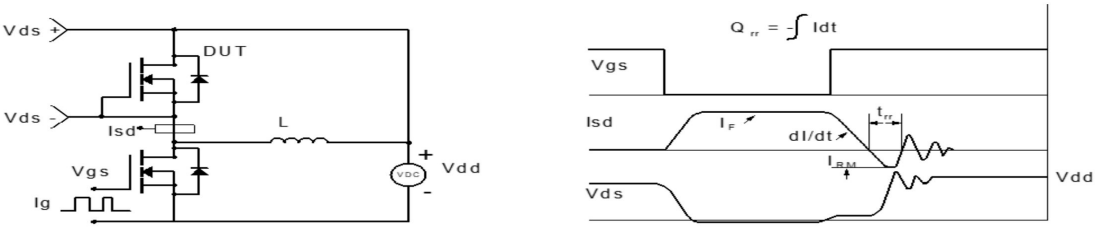
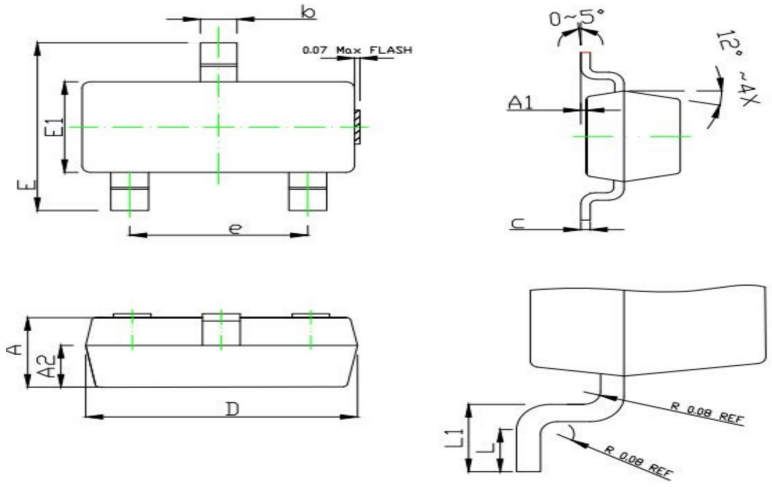


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23)



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.95	1.00	1.05
A1	0.01	0.05	0.10
b	0.35	0.40	0.45
c	0.11 BSC		
D	2.80	2.90	3.00
E	2.30	2.40	2.50
E1	1.20	1.30	1.40
e	1.90 BSC		
L	0.20	–	–
L1	0.30	0.40	0.50
A2	0.60 REF		